

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>	Docket Number 204552016410	Application Number NEW
	Applicant Toshiyuki OKUMURA	
	Filing Date January 17, 2002	Group Art Unit not assigned
	Mailing Date January 17, 2002	

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U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES	NO
C/12/1	1.	10/1988	63-257286 A	Japan			abs.	
	2.	6/1990	2-168746	Japan				X
	3.	6/1996	EP 0 716 457 A2	EPO			X	
	4.	10/1996	08-264902 A	Japan			abs.	
	5.	11/1996	08-316528 A	Japan			abs.	
	6.	11/1996	08-316563	Japan			abs.	
	7.	12/1996	EP 0 746 067 A1	EPO			X	
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(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
C/12/1	14.	"Ridge-geometry InGa _N multi-quantum-well-structure laser diodes," by Shuji NAKAMURA et al., Appl. Phys. Lett. 69 (10), 2 September 1996, American Institute of Applied Science, pp: 1477-9
	15.	Applied Physics Letters, Vol. 69, No. 20, Page 3034-3036 entitled Continuous-Wave Operation of InGa _N Multi-Quantum-Well-Structure Laser Diodes at 233 K, S. Nakamura et al.
C/12/1	16.	DATABASE WPI Section Ch, Week 9027 Derwent Publications Ltd., London, GB; Class A88, AN 90-204849 XP 002111575 & JP 02 135141 A (TOYOBO KK), 24 May 1990 (1990-05-24) *abstract*

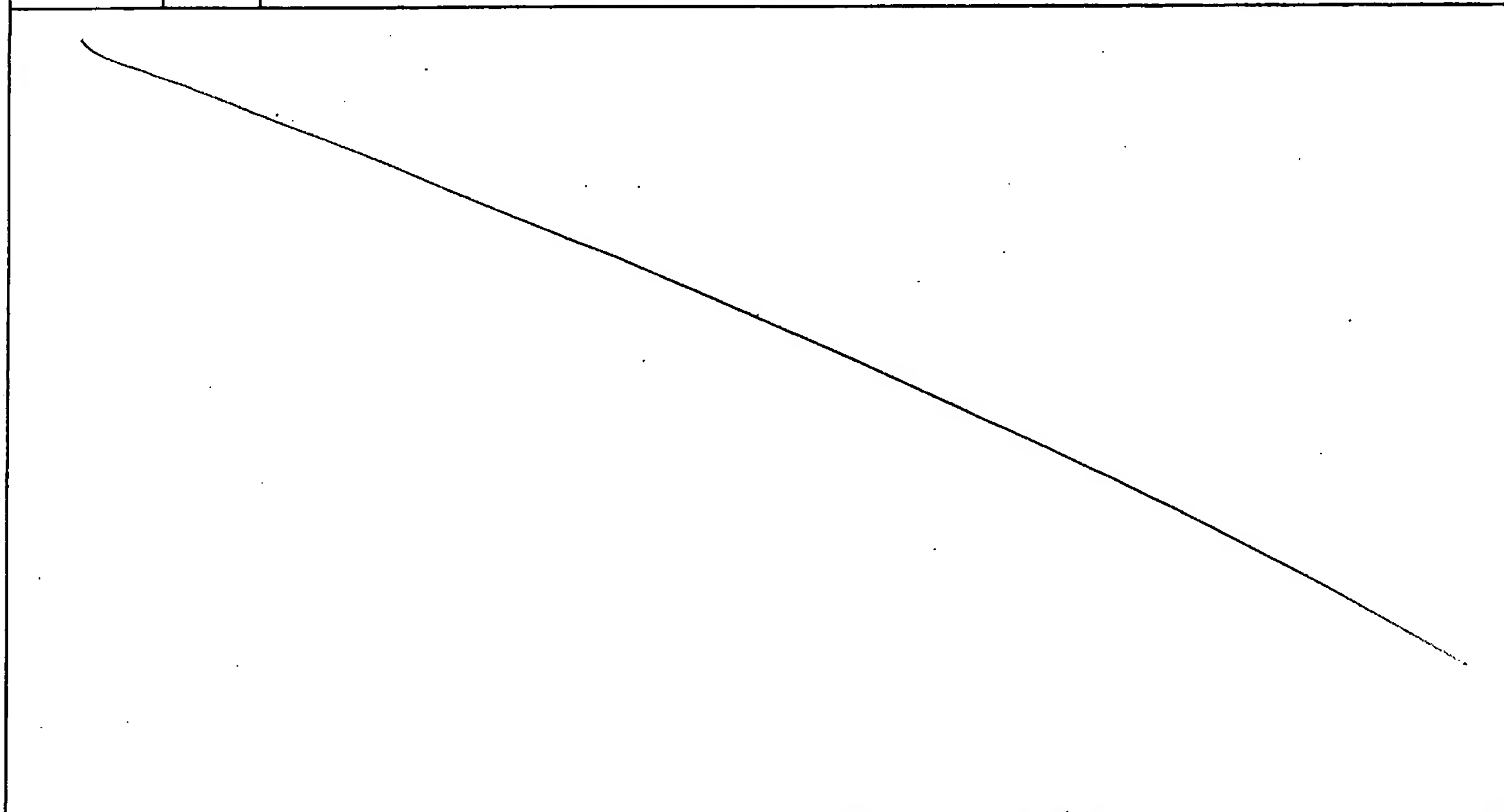
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C/10	17.	Patent Abstracts of Japan Vol. 018, No. 673 (E-1647), December 19, 1994 (1994-12-19) & JP 06 268257 A (Nichia Chem Ind. Ltd), September 22, 1994)
	18.	Kortel: "Interaction of the Dopants MG and SI In Alxga-XAS/GAAS Heterolayers (MOVPE): Application to DQW Laser Structures" Journal of Crystal Growth, NL, North-Holland Publishing Co., Amsterdam, Vol. 107, No. 1 /04, January 1, 1991, Pages 779-783, XP000246687
	19.	Chen Q. et al: "UV, Blue and Green Light Emitting Diodes Based on GaN-InGan Multiple Quantum Wells Over Sapphire And (111) Spinel Substrates" Materials Science And Engineering B, Ch. Elsevier Sequoia, Lausanne, Vol. 43, No. 1-3, January 1, 1997 Pages 265-268
	20.	Laidig W. D. et al.: "Properties of INXGAI-XAS-GAAS Strained-Layer Quantum-Well-Heterostrcuture Injection Lasers" Journal of Applied Physics, US, American Institute of Physics. New York, Vol. 57, No. 1 January 1985, Pages 33-38
	21.	Patent Abstracts of Japan Vol. 017, No. 453 (E-1417), August 19, 1993 & JP 05 102604 April 23, 1993
Qd q	22.	Itaya K. et al.: "Room Temperature Pulsed Operation of Nitride Based Multi-Quantum-Well Laser Diodes With Cleaved Facets on Conventional C-Face Sapphire Substrates" Japanese Journal of Applied Physics, JP, Publication Office Japanese Journal of Applied Physics. Tokyo, Vol. 35, No. 10B, Part 02, October 15, 1996 Pages L1315-L1317



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